# 16 $\Omega$ , Low Parasitic Capacitance and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

### **DESCRIPTION**

The DG411LE, DG412LE, and DG413LE are monolithic quad single-pole-single-throw analog switches. The DG411LE and DG412LE differ only in that they respond to opposite logic levels. The DG413LE has two normally open and two normally closed switches. It can be given various configurations, including four SPST, two SPDT, and one DPDT.

The DG411LE, DG412LE, and DG413LE offer low on resistance of 16  $\Omega$ , low parasitic capacitance of 15 pF switch on capacitance, and low charge injection over the signal swing range.

The DG411LE, DG412LE, and DG413LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with  $\pm$  3 V to  $\pm$  8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG411LE, DG412LE, and DG413LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

#### **FEATURES**

 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply



• On-resistance  $R_{DS(on)}$ : 16  $\Omega$ 

• Low parasitic capacitance:

C<sub>D(ON)</sub>: 15 pF C<sub>S(OFF)</sub>: 5 pF

 Less than 8 pC charge injection over the full signal swing range

 Fast switching t<sub>ON</sub>: 16 ns t<sub>OFF</sub>: 9 ns

• TTL, CMOS compatible

 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

#### **BENEFITS**

- Wide operation voltage range
- Low signal errors and distortion
- · Fast switching time
- Minimized switching glitch

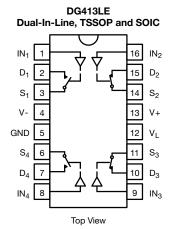
### **APPLICATIONS**

- · Automatic test equipment
- · Data acquisition systems
- Meters and instruments
- Medical and healthcare systems
- Communication systems
- · Audio and video signal routing
- Relay replacement
- Battery powered systems
- Computer peripherals
- · Audio and video signal routing

### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**

**Dual-In-Line, TSSOP and SOIC** IN₁ IN<sub>2</sub>  $D_2$ D₁ Sı  $S_2$ V-V٠  $V_L$ **GND**  $S_4$  $S_3$  $D_4$  $D_3$  $IN_4$ Top View

DG411LE, DG412LE



Document Number: 78091



# DG411LE, DG412LE, DG413LE

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TRUTH TABLE								
LOGIC	DG411LE	DG412LE						
0	ON	OFF						
1	OFF	ON						

Logic "0"  $\leq$  0.8 V Logic "1"  $\geq$  2.4 V

TRUTH TABLE							
LOGIC	SW <sub>1</sub> , SW <sub>4</sub>	SW <sub>2</sub> , SW <sub>3</sub>					
0	OFF	ON					
1	ON	OFF					

Logic "0"  $\leq$  0.8 V Logic "1"  $\geq$  2.4 V

ORDERING INFORMATION								
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY				
		16 min T000D	DG411LEDQ-GE3	Tube 360 units				
		16-pin TSSOP	DG411LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG411LE	16 nin SOIC	DG411LEDY-GE3	Tube 500 units				
		16-pin SOIC	DG411LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG411LEDJ-GE3	Tube 500 units				
		16-pin TSSOP -	DG412LEDQ-GE3	Tube 360 units				
40.004 05.00			DG412LEDQ-T1-GE3	Tape and reel, 3000 units				
-40 °C to +85 °C Lead-free	DG412LE		DG412LEDY-GE3	Tube 500 units				
2000 1100		16-ріп 3010	DG412LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG412LEDJ-GE3	Tube 500 units				
		16 pin TOOOD	DG413LEDQ-GE3	Tube 360 units				
		16-pin TSSOP	DG413LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG413LE	16-pin SOIC	DG413LEDY-GE3	Tube 500 units				
		10-рін 3010	DG413LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG413LEDJ-GE3	Tube 500 units				

ABSOLUTE MAXIMUM RATING	as .			
PARAMETER		LIMIT	UNIT	
V+ to V-		-0.3 to +18		
GND to V-		18		
V <sub>L</sub>		(GND -0.3) to (V+) +0.3	V	
I <sub>N</sub> a, V <sub>S</sub> , V <sub>D</sub>		-0.3 to (V+) +0.3 or 30 mA, whichever occurs first		
Continuous Current (Any terminal)		30	A	
Peak Current, S or D (Pulsed 1 ms, 10 % d	uty cycle)	100	- mA	
Storage Temperature	(DQ, DY suffix)	-65 to +125	°C	
Storage Temperature	(AK suffix)	-65 to +150	7	
	16-pin TSSOP °	450		
Power Dissipation (Packages) b	16-pin SOIC <sup>d</sup>	650	mW	
16-pin CerDIP <sup>e</sup>		900		
ESD Human Body Model (HBM); per ANSI	/ ESDA / JEDEC® JS-001	2500	V	
Latch Up Current, per JESD78D		400	mA	

#### Notes

- a. Signals on S<sub>X</sub>, D<sub>X</sub>, or IN<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 75 °C
- d. Derate 7.6 mW/°C above 75 °C
- e. Derate 12 mW/°C above 75 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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SPECIFICATIONS a (	Single Su	pply 12 V)							
PARAMETER	SYMBOL			TYP. °	LIM	IFFIX IITS +125 °C	LIM	IFFIX IITS o +85 °C	UNIT
		$V_{L} = 12 \text{ V}, V_{T} = 0 \text{ V}$ $V_{L} = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{f}$			MIN. d	MAX. d	MIN. d	MAX.d	
Analog Switch	•								
Analog Signal Range e	V <sub>ANALOG</sub>		Full	-	0	12	0	12	V
Drain-Source	D	V+ = 10.8 V, V- = 0 V	Room	16	-	26	-	26	Ω
On-Resistance	R <sub>DS(on)</sub>	$I_S = 10 \text{ mA}, V_D = 2/9 \text{ V}$	Full	-	ı	40	-	35	5.2
	la, m		Room	-	-1	1	-1	1	
Switch Off Leakage Current	I <sub>S(off)</sub>	V <sub>D</sub> = 1/11 V, V <sub>S</sub> = 11/1 V	Full	-	-15	15	-10	10	
Switch On Leakage Ourient	la	VD = 1/11 V, VS = 11/1 V	Room	-	-1	1	-1	1	nA
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	II/A
Channel On Leakage	l= ( )	$V_S = V_D = 11/1 V$	Room	=	-1	1	-1	1	
Current	I <sub>D(on)</sub>		Full	-	-15	15	-10	10	
Digital Control									
Input Current, VIN Low	I <sub>IL</sub>	V <sub>IN</sub> under test = 0.8 V	Full	0.01	-1.5	1.5	-1	1	μA
Input Current, VIN High	I <sub>IH</sub>	$V_{IN}$ under test = 2.4 V	Full		-1.5	1.5	-1	1	μΑ
Dynamic Characteristics									
Turn-On Time	tou	$R_L = 300 \Omega$ , $C_L = 35 pF$ , $V_S = 5 V$ , see figure 2	Room	16	ı	50	-	50	
Turri-On Time	t <sub>ON</sub>		Full	-	ı	70	-	60	
Turn-Off Time	+		Room	9	ı	30	-	30	ns
rum-on rime	t <sub>OFF</sub>		Full	-	-	48	-	40	
Break-Before-Make Time Delay	t <sub>D</sub>	DG413L only, $V_S = 5 V$ , $R_L = 300 \Omega$ , $CL = 35 pF$	Room	5	-	-	-	-	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	6.6	-	-	-	-	рС
Off-Isolation e	OIRR		Room	68.4	-	-	-	-	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$	Room	114	-	-	-	-	dB
Source Off Capacitance e	C <sub>S(off)</sub>		Room	5	-	-	-	-	
Drain Off Capacitance e	C <sub>D(off)</sub>	f = 1 MHz	Room	6	-	-	-	-	pF
Channel-On Capacitance e	C <sub>D(on)</sub>		Room	15	-	-	-	-	
Power Supplies									
Positive Supply Current	I+		Room	0.02	-	1	-	1	
1 Ositive Supply Culterit	1+		Full	-	-	7.5	-	5	
Negative Supply Current	I-		Room	-0.002	-1	-	-1	-	
- Nogative Supply Sufferit	I-	V <sub>IN</sub> = 0 V or 5 V	Full	-	-7.5	-	-5	-	,.,
Logic Supply Current	1.	VIN = O V OI O V	Room	0.002	-	1	-	1	μA
Logic Supply Current	ال		Full	-	-	7.5	-	5	
Ground Current	I <sub>GND</sub>		Room	-0.002	-1	-	-1	-	
Circuita Current			Full	-	-7.5	-	-5	-	

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- e. Guaranteed by design, not subject to production test
- f. V<sub>IN</sub> = input voltage to perform proper function
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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PARAMETER   SYMBOL	SPECIFICATIONS a (Dual Supply ± 5 V)									
Malog Switch   Malog Switch   Malog Signal Range   Value	PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED	TEMP.b TYP.c		LIMITS		LIN	IITS	UNIT
Analog Signal Range   Nanalog   Nanalog   Para   Nanalog   Para   Nanalog						MIN. d	MAX. d	MIN. d	MAX. d	
Drain-Source On-Resistance   Rosero	Analog Switch	1		<u> </u>			L	L	L	
Name	Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-5	5	-5	5	V
Service   Ser		R <sub>DS(on)</sub>			18	-		-		Ω
Switch Off Leakage Current 9   V = 5.5, V = -5.5 V, V = ± 4.5 V   Full  15   15   -10   10   10   10   10   10   10   1	On-Resistance	Bo(on)	$I_S = 10 \text{ mA}, V_D = \pm 3.5 \text{ V}$	-	-	-		-		
Switch Off   Policy   Polic		Is(off)			-	·		-		
Digital Control   Digital C		O(OII)			-					
Channel On Leakage Current 9   Indicate   V+ = 5.5 V, V- = -5.5 V, Vo = -5.5 V,	Leakage Current 9	Intoffi	$V_D = \pm 4.5 \text{ V}, V_S = \pm 4.5 \text{ V}$		-			-		nA
Deal		·D(011)		Full	-			_		
Digital Control   Full   Control   Control   Control   Full   Control   Control   Control   Full   Control   Control   Control   Full   Control   Cont		In(an)		Room	-	-1	1	-1	1	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Leakage Current <sup>g</sup>	וי (on)	$V_{S} = V_{D} = \pm 4.5 \text{ V}$	Full	-	-15	15	-10	10	
Input Current, V <sub>IN</sub> High e   I <sub>IH</sub>   V <sub>IN</sub> under test = 2.4 V   Full   0.05   -1.5   1.5   -1   1   PA	Digital Control									
Input Current, V <sub>IN</sub> High e   V <sub>IN</sub> under test = 2.4 V   Full   0.05   -1.5   1.5   -1   1   V <sub>IN</sub>	Input Current, V <sub>IN</sub> Low <sup>e</sup>	I <sub>IL</sub>	V <sub>IN</sub> under test = 0.8 V	Full	0.05	-1.5	1.5	-1	1	
Turn-On Time ° to N Turn-Off Time ° to FF  T	Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.05	-1.5	1.5	-1	1	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Dynamic Characteristics									
Turn-Off Time e   Turn-Off	T O . T' 0			Room	17	-	50	-	50	
Turn-Off Time e   Topf   Turn-Off Time e   Turn-Off Time e   Topf   Turn-Off Time e	Turn-On Time 9			Full	-	-	70	-	60	
Full   -   -   50   -   40				Room	12	-	35	-	35	ne
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>		Full	-	-	50	-	40	115
		t <sub>D</sub>	DG413L only, $V_S = 3.5 \text{ V}$ , $R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$	Room	5	-	-	-	-	
OIFI solation e	Charge Injection e	Q	$V_q = 0 \text{ V}, R_q = 0 \Omega, C_L = 10 \text{ nF}$	Room	5.8	-	-	-	-	рС
Room   113   -   -   -   -	Off Isolation e	OIRR		Room	68	-	-	-	-	
Drain Off Capacitance e   C <sub>D(off)</sub>   F = 1 MHz   Room   6   -   -   -   -   -		X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$	Room	113	-	-	-	-	dB
Drain Off Capacitance e   C <sub>D(off)</sub>   f = 1 MHz   Room   6   -   -   -   -   -     PF	Source Off Capacitance e	C <sub>S(off)</sub>		Room	5	-	-	-	-	
Channel On Capacitance	Drain Off Capacitance e		f = 1 MHz	Room	6	-	-	=.	-	рF
Power Supplies  Positive Supply Current e  I+  Negative Supply Current e  Logic Supply Current e  I_L  Ground Current e  Room   0.03   -   1   -   1     Full   -   -   7.5   -   5     Room   -0.002   -1   -   -1   -   Full   -   -7.5   -   5   -   Room   0.002   -   1   -   1     Full   -   -   7.5   -   5     Room   0.002   -   1   -   1   Full   -   -   7.5   -   5   Room   -0.002   -1   -   -1   -	Channel On Capacitance e			Room	14	-	-	-	-	
Positive Supply Current e I+  Negative Supply Current e I-  Logic Supply Current e I <sub>L</sub> Ground Current e I <sub>L</sub> Room 0.03 - 1 - 1  Full 7.5 - 5  Room -0.002 -11  Full7.5 - 5  Room 0.002 - 1 - 1  Full 7.5 - 5  Room -0.002 -1 - 1  Full 7.5 - 5  Room -0.002 -1 - 1  Full 7.5 - 5	·	_(=::)						I		
Negative Supply Current e I-  Logic Supply Current e I <sub>L</sub> Room 0.002 -11 -  Full7.5 - 5  Room 0.002 - 1 - 1  Full7.5 - 5  Room 0.002 - 1 - 1  Full7.5 - 5  Room 0.002 - 1 - 1  Full5  Room 0.002 - 1 - 1	• •			Room	0.03	-	1	_	1	
Negative Supply Current e   I-   V <sub>IN</sub> = 0 V or 5 V     Room   -0.002   -1   -   -1   -	Positive Supply Current e	l+		Full	-	-	7.5	-	5	
Negative Supply Current e   I-   V <sub>IN</sub> = 0 V or 5 V   Full   -   -7.5   -   -5   -				Room	-0.002	-1		-1	-	
Logic Supply Current e   I <sub>L</sub>	Negative Supply Current <sup>e</sup>	I-				·	-	-	_	
Logic Supply Current e			$V_{IN} = 0 \text{ V or 5 V}$		ļ					μΑ
Ground Current e	Logic Supply Current <sup>e</sup>	ΙL			-	_				
Ground Current e					-0.002	-1			-	
	Ground Current e	I <sub>GND</sub>		Full		-7.5	_	-5	_	

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SPECIFICATIONS a	SPECIFICATIONS a (Single Supply 5 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		LIM	IFFIX IITS o +85 °C	UNIT
		V+ = 5 V, V- = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-	5	1	5	٧
Drain-Source	B-a/	V+ = 4.5 V,	Room	36	-	50	ı	50	Ω
On-Resistance e	R <sub>DS(on)</sub>	$I_S = 5 \text{ mA}, V_D = 1 \text{ V}, 3.5 \text{ V}$	Full	-	-	88	-	75	22
Dynamic Characteristics									
Turn-On Time e	t <sub>ON</sub>		Room	27	-	50	ı	50	
Turn-Off Time	rON	$R_L = 300 \Omega, C_L = 35 pF,$	Hot	-	-	90	-	60	
Turn-Off Time e	t <sub>OFF</sub>	$V_S = 3.5 V$ , see figure 2	Room	15	-	30	ı	30	ns
Turn-Oil Time		UFF		Hot	-	-	55	ı	40
Break-Before-Make Time Delay <sup>e</sup>	t <sub>D</sub>	DG413L only, $V_S$ = 3.5 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room	11	-	-	-	-	
Charge Injection <sup>e</sup>	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	3.3	-	-	-	-	рС
Power Supplies									
Positive Supply Current e	l+		Room	0.02	-	1	1	1	
Fositive Supply Current	1+		Hot	-	-	7.5	-	5	
Negative Supply Current e	I-		Room	-0.002	-1	-	-1	-	
Negative Supply Current	I-	$V_{IN} = 0 \text{ V or } 5 \text{ V}$	Hot	-	-7.5	-	-5	-	
Logic Supply Current e	I.	V <sub>IN</sub> = 0 V Or 5 V	Room	0.002	-	1	-	1	μΑ
Logic Supply Current	ΙL		Hot	-	-	7.5	-	5	
Ground Current e	laura		Room	-0.002	-1	-	-1	-	
Ground Gurrent -	I <sub>GND</sub>		Hot	-	-7.5	-	-5	-	

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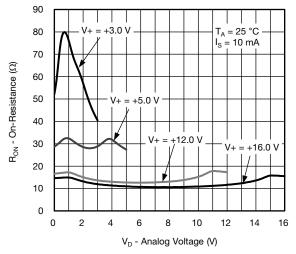


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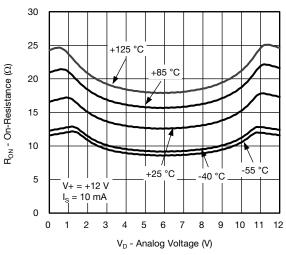
SPECIFICATIONS a	(Single Su	oply 3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE OL SPECIFIED		TYP. °	-55 °C	X LIMITS to +125 C	LIM	IFFIX IITS o +85 °C	UNIT
		V+ = 3 V, V- = 0 V $V_L = 3 V, V_{IN} = 0.4 V, 2.0 V^f$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch	•				•				
Analog Signal Range e	V <sub>ANALOG</sub>		Full	-	0	3	0	3	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V+ = 2.7  V, V- = 0  V, $I_S = 5 \text{ mA}, V_D = 0.5, 2.2 \text{ V}$	Room Full	106	-	130 150	-	130 140	Ω
		, , ,	Room	_	-1	1	-1	1	
Switch Off	I <sub>S(off)</sub>	V+ = 3.3. V- = 0 V.	Full	_	-15	15	-10	10	
Leakage Current <sup>g</sup>		$V_{D} = 1, 2 \text{ V}, V_{S} = 2, 1 \text{ V}$	Room	_	-1	1	-1	1	
-	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	nA
Channel On		V+ = 3.3 V. V- = 0 V.	Room	-	-1	1	-1	1	
Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	$V_S = V_D = 1, 2 V$	Full	-	-15	15	-10	10	
Digital Control				L		l			
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>IN</sub> under test = 0.4 V	Full	0.005	-1.5	1.5	-1	1	
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.005	-1.5	1.5	-1	1	μA
Dynamic Characteristics									
Turn-On Time	<b>+</b>			57	-	85	-	85	
rum-on nine	t <sub>ON</sub>	$R_L = 300 \Omega, C_L = 35 pF,$	Full	-	-	150	-	110	
Turn-Off Time	t <sub>OFF</sub>	$V_S = 1.5 V$ , see figure 2	Room	25	-	60	ı	60	ns
rum-on rime	OFF		Full	-	-	100	-	85	
Break-Before-Make Time Delay	t <sub>D</sub>	DG413L only, $V_S = 1.5 \text{ V}$ , $R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$	Room	24	-	-	-	-	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	2	-	-	-	-	рС
Off Isolation e	OIRR		Room	68	-	-	-	-	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$	Room	107	-	-	-	-	dB
Source Off Capacitance e	C <sub>S(off)</sub>		Room	6	-	-	-	-	
Drain Off Capacitance e	C <sub>D(off)</sub>	f = 1 MHz	Room	7		-	-	-	pF
Channel On Capacitance e	C <sub>D(on)</sub>		Room	15	-	-	-	-	

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- f.  $V_{IN}$  = input voltage to perform proper function
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test

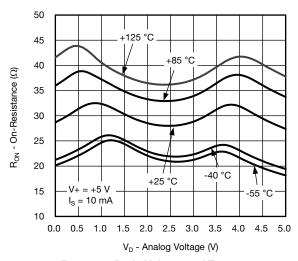
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



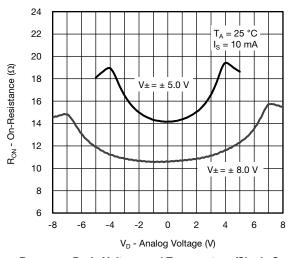
R<sub>DS(on)</sub> vs. Drain Voltage (Single Supply)



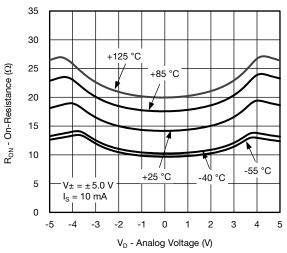
R<sub>DS(on)</sub> vs. Drain Voltage and Temperature



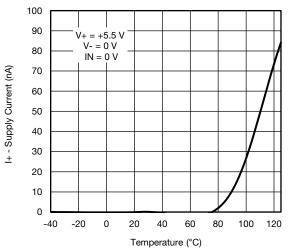
 $R_{DS(on)}$  vs. Drain Voltage and Temperature



R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Single Supply)

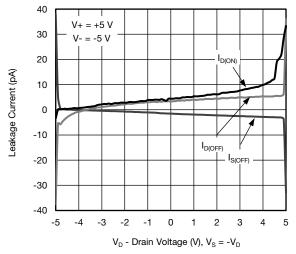


Supply Current vs. Temperature

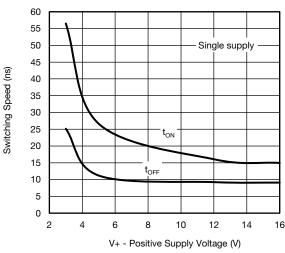


Switching Time vs. Single Supply

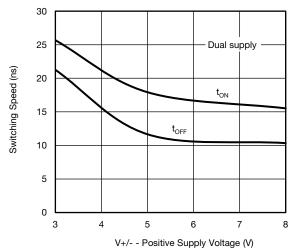
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



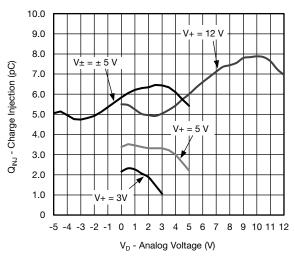
Leakage Current vs. Drain Voltage



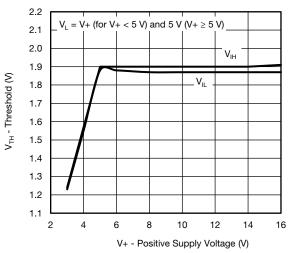
Switching Time vs. Single Supply Voltage



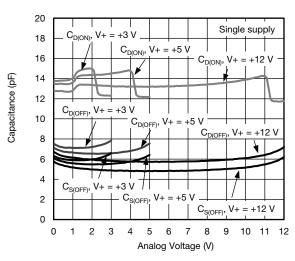
Switching Time vs. Dual Supply Voltage



Charge Injection vs. Drain Voltage



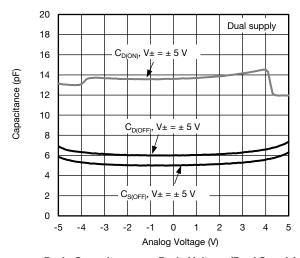
Threshold vs. Single Supply Current



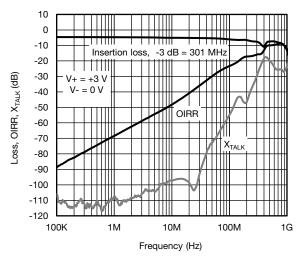
Drain Capacitance vs. Drain Voltage (Single Supply)

Vishay Siliconix

# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

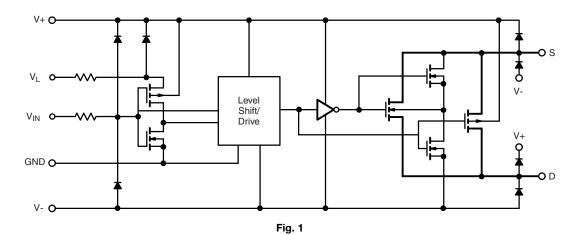




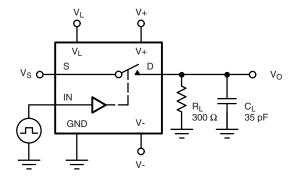


Insertion Loss, Off Isolation and Crosstalk vs. Frequency

### **SCHEMATIC DIAGRAM** (Typical Channel)

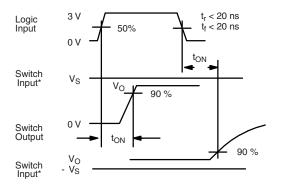


### **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_O = V_S$$
 
$$\frac{R_L}{R_L + r_{DS(on)}}$$



Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Fig. 2 - Switching Time

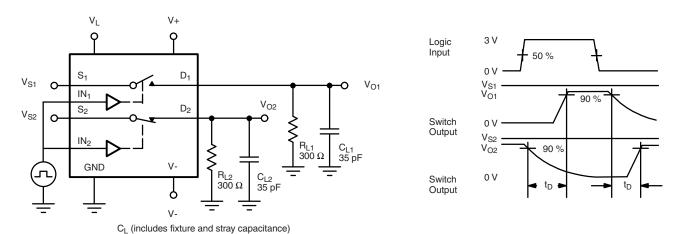
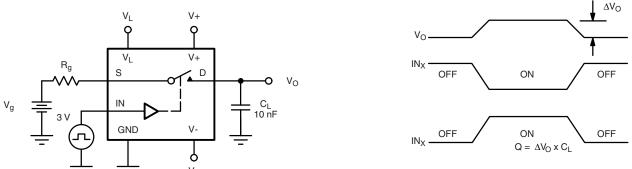


Fig. 3 - Break-Before-Make (DG413LE)



 $\ensuremath{\mathsf{IN}}_X$  dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection

### **TEST CIRCUITS**

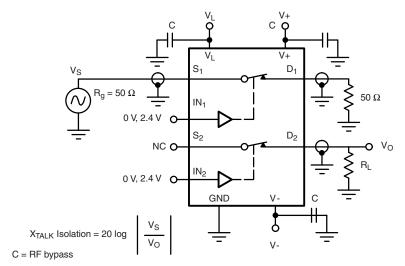


Fig. 5 - Crosstalk

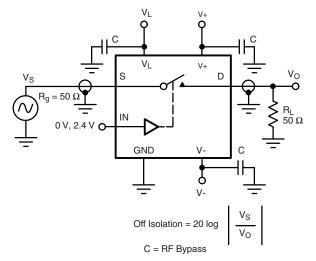


Fig. 6 - Off-Isolation

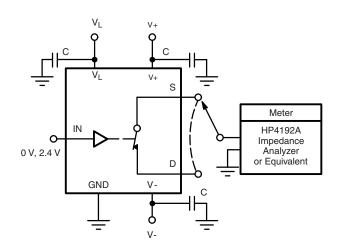


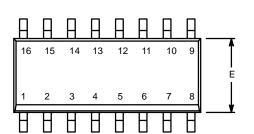
Fig. 7 - Source / Drain Capacitances

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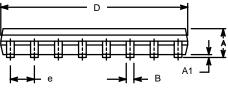
SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012

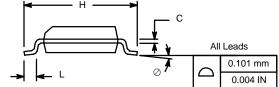


	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
В	0.38	0.51	0.015	0.020
С	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
0	0°	8°	0°	8°
ECNI CO	2046 Day F	00 1.1.04		

ECN: S-03946-Rev. F, 09-Jul-01

DWG: 5300

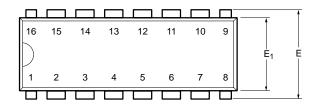


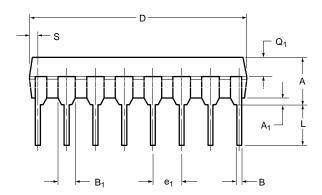


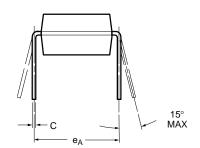
www.vishay.com 02-Jul-01



PDIP: 16-LEAD





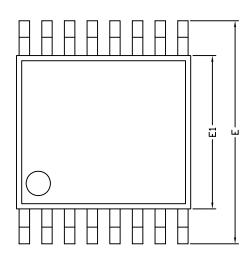


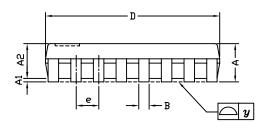
	MILLIN	ILLIMETERS INCHES				
Dim	Min	Max	Min	Max		
Α	3.81	5.08	0.150	0.200		
A <sub>1</sub>	0.38	1.27	0.015	0.050		
В	0.38	0.51	0.015	0.020		
B <sub>1</sub>	0.89	1.65	0.035	0.065		
С	0.20	0.30	0.008	0.012		
D	18.93	21.33	0.745	0.840		
Е	7.62	8.26	0.300	0.325		
E <sub>1</sub>	5.59	7.11	0.220	0.280		
e <sub>1</sub>	2.29	2.79	0.090	0.110		
e <sub>A</sub>	7.37	7.87	0.290	0.310		
L	2.79	3.81	0.110	0.150		
$Q_1$	1.27	2.03	0.050	0.080		
S	0.38	1.52	.015	0.060		
ECN: S-03946—Rev. D, 09-Jul-01						

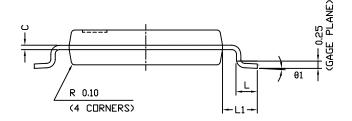
Document Number: 71261 www.vishay.com 06-Jul-01 1



**TSSOP: 16-LEAD** 







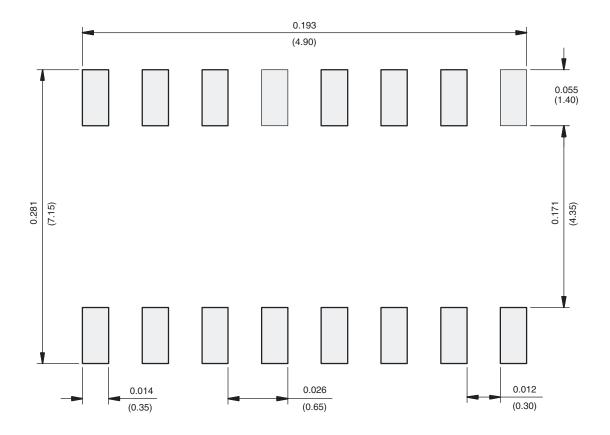
	DIMENSIONS IN MILLIMETERS							
Symbols	Min	Nom	Max					
А	-	1.10	1.20					
A1	0.05	0.10	0.15					
A2	-	1.00	1.05					
В	0.22	0.28	0.38					
С	-	0.127	-					
D	4.90	5.00	5.10					
E	6.10	6.40	6.70					
E1	4.30	4.40	4.50					
е	-	0.65	-					
L	0.50	0.60	0.70					
L1	0.90	1.00	1.10					
у	-	-	0.10					
θ1	0°	3°	6°					
FCN: S-61920-Rev. D. 23-	Oct-06							

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



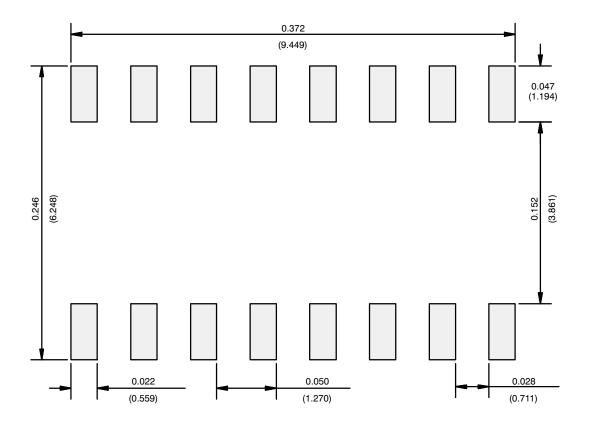
### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



Recommended Minimum Pads Dimensions in inches (mm)



### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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Vishay

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